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Applicati n Number	09/751,423					
Filing Dat	December 29, 2000					
First Named Inventor	Robert A. Morgan					
Art Unit	2814					
Examiner Name	Douglas A. Willie					
Attorney Docket Number	H16 26549 US					

U.S. PATENT DOCUMENTS							
	Cite No.1	Document Number		5	Name of Patentee or	Pages, Columns, Lines Where	
Examiner Initials*			Applicant of Cited Document	Relevant Passages or Relevant Figures Appear			
Dow		US	5,034,958		07-23-1991	Kwon et al.	
7		US	5,258,316	Α	11-02-1993	Ackley et al.	
		U\$	6,026,111	Α	02-15-2000	Jlang et al.	
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Initials	No.¹	Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (If known)		Document	Passages or Relevant Figures Appear	١ '
	1	EP	0 712 182	A2	05-15-1996	Sharp Kabushiki Kaisha		
	_	FR	2 768 566	A1	03-19-1999	France Telecon Society Anonyme		
$\neg T$	,	wo	99/031735	A1	06-24-1999	Honeywell Inc.		
		wo	00/045483	A1	08-03-2000	University of Sheffield		

Examiner - Signature	Coe	ga a	lesto	Date Considered	1 dee 03

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Sheet	2 01 2	Examiner Name	Douglas A. Willie	
		Attorney Docket Number	H16 26549 US	

	OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS							
Examiner Initials*	Cite No.¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	L,					
Dhe		International Search Report, dated 03-12-2003, relative to PCT application No. PCT/US 01/50214, the foreign equivalent to the instant U.S. application 09/751,423.						
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Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is attached.

FORM PTO-1449	Atty. Docket No.: 1100.1114101 (H16-26549)	Serial No.: 09/751,423	
OTHER OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION	Applicant: Robert A. Morgan et al.		
DISCLOSURE STATEMENT	Filing Date	Group Art:	
AUS 1 9 2003 (2)	December 29, 2000	2872	

_	7911		
0	Dela	BB	Choquette et al., "Lithographically-Defined Gain Apertures Within Selectively Oxidized VCSELs", paper CtuL6, Conference on Lasers and Electro-Optics, San Francisco, California (2000).
•		вс	Oh, T. H. et al., "Single-Mode Operation in Antiguided Vertical-Cavity Surface-Emitting Laser Using a Low-Temperature Grown AlGaAs Dielectric Aperture", <u>IEEE Photon. Technol. Lett.</u> 10(8), 1064-1066 (1998).
O	5	BD	"Surface-Emitting Microlasers for Photonic Switching and Interchip Connections", Optical Engineering, 29, pp. 210-214, March 1990.
•		BE	G. Shtengel et al., "High-Speed Vertical-Cavity Surface-Emitting Lasers", Photon. Tech. Lett., Vol. 5, No. 12, pp. 1359-1361 (December 1993).
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EXAMINER: 1 Deag as 4 12 | DATE CONSIDERED: 1 Lee 03

FORM PTO-1449	Atty. Docket No.: 1100.1114101 (H16-26549)	Serial No.: 09/751,423	
LISTOF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION	Applicant: Robert A. Morgan et al.		
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8	RADEM	AFRICAS I	U.S.	PATENT DOC	UMENTS			
Exa	miner itial	Document No.	Date	Name		Sub Class	Filing Date If Appropriate	
Notu	AA	4,317,085	02/23/1982	Brunham et al.	372	50		
	AB	4,466,694	08/21/1984	MacDonald	385	37		
	AC	4,660,207	04/21/1987	Svilans	372	45		
$\int_{-\infty}^{\infty}$	AD	4,784,722	11/15/1988	Liau et al.	156	649		
$\perp$	AE	4,885,592	12/05/1989	Kofol et al.	343	753		
	AF	4,901,327	02/13/1990	Bradley	372	45		
	AG	4,943,970	07/24/1990	Bradley	372	45		
	АН	4,956,844	09/11/1990	Goodhue et al.	372	44		
$I_{-}$	ΑI	5,031,187	07/09/1991	Orenstein et al.	372	50		
$I_{-}$	AJ	5,052,016	09/24/1991	Mahbobzadeh	372	96		
<u></u>	AK	5,056,098	10/08/1991	Anthony et al.	372	45		
	AL	5,062,115	10/29/1991	Thornton	372	50		
	AM	5,068,869	11/26/1991	Wang et al.	372	45		
	AN	5,115,442	05/19/1992	Lee et al.	372	45		
	AO	5,140,605	08/18/1992	Paoli et al.	372	50		
	AP	5,158,908	10/27/1992	Blonder et al.	437	129	<u></u>	
	AQ	5,216,263	06/01/1993	Paoli	257	88		
$\bot$	AR	5,216,680	06/01/1993	Magnusson et	al. 372	20		
	AS	5,237,581	08/17/1993	Asada et al.	372	45		
	AT	5,245,622	09/14/1993	Jewell et al.	372	45		
	AU	5,258,990	11/02/1993	Olbright et al.	372	46		
	AV	5,285,466	02/08/1994	Tabatabaie	372	92		
$\overline{\Gamma}$	AW	5,293,392	03/08/1994	Shieh et al.	372	45		
	AX	5,317,170	05/31/1994	Paoli	257	88		
	AY	5,317,587	05/31/1994	Ackley et al.	372	45		

Atty. Docket No.:
1100.1114101 (H16-26549)

Applicant: Robert A. Morgan et al.

Applicant: Serial No.:
09/751,423

Applicant: Robert A. Morgan et al.

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Exan Init		Document No.	Date	Name	Class	Sub Class	Filing Date If Appropriate
The	AZ	5,325,386	06/28/1994	Jewell et al.	372	50	
	BA	5,331,654	07/19/1994	Jewell et al.	372	45	
	BB	5,337,074	08/09/1994	Thornton	346	107R	
	ВС	5,349,599	09/20/1994	Larkins	372	50	
$\mathcal{I}_{-}$	BD	5,351,256	09/27/1994	Schneider et al.	372	45	
	BE	5,359,447	10/25/1994	Hahn et al.	359	154	
	BF	5,359,618	10/25/1994	Lebby et al.	372	45	
	BG	5,363,397	11/08/1994	Collins et al.	372	92	
	вн	5,373,520	12/13/1994	Shoji et al.	372	45	
	BI	5,404,373	04/04/1995	Cheng	372	50	
T	вл	5,416,044	05/16/1995	Chino et al.	437	129	
	вк	5,428,634	06/27/1995	Bryan et al.	372	45	
	BL	5,446,754	08/29/1995	Jewell et al.	372	50	
	вм	5,475,701	12/12/1995	Hibbs-Brenner	372	50	
	BN	5,513,202	04/30/1996	Kobayashi et al.	372	96	
	во	5,530,715	06/25/1996	Shieh et al.	372	96	
	BP	5,555,255	09/10/1996	Kock et al.	372	96	
	BQ	5,557,626	09/17/1996	Grodinski et al.	372	45	
	BR	5,561,683	10/01/1996	Kwon	372	96	
	BS	5,568,499	10/22/1996	Lear	372	45	
	вт	5,598,300	01/28/1997	Magnusson et al.	359	566	
	BU	5,606,572	02/25/1997	Swirhun et al.	372	96	
$\int$	BV	5,642,376	06/24/1997	Olbright et al.	372	45	
$\overline{I}$	BW	5,727,013	03/10/198	Botez et al.	372	96	
	вх	5,774, <u>4</u> 87	06/30/1998	Morgan	372	45	

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FORM PTO-1449	Atty. Docket No.: 1100.1114101 (H16-26549)	Serial No.: 09/751,423	
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION	Applicant: Robert A. Morgan et al.		
DISCLOSURE STATEMENT	Filing Date	Group Art:	
MIG 1 9 2000 2	December 29, 2000	2872	

## FOREIGN PATENT DOCUMENTS

•		Document No.	Date	Country	Class	Sub Class	Translation Yes No	
Dhei	AA	DE 4 240 706 A	06/09/1994	Germany				
	AB	EP 0 288 184 A	10/26/1988	Europe				
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	AC	EP 0 776 076 A	05/28/1997	Europe				
	AD	JP 60-123084 A	07/01/1985	Japan			Yes (Abstract only	
	AE	JP 02-054981 A	02/23/1990	Japan			Yes (Abstract only	
	AF	Guenter et al., "Reliab	ility of Proton- ASE 96; Photo	uthor, Title, Date, Perti Implanted VCSELs for onics West: Fabrication wham, WA 1996).	Data Com	nunication	s", Invited paper, lity of	
AG Hibbs-Brenner et al., "Performance, Uniformity and Yield of 8 MOVPE", IEEE Phot. Tech. Lett., Vol. 8, No. 1, pp. 7-9, Janua		f 850nm V( nuary 1996.	850nm VCSELs Deposited by ary 1996.					
	AH Hornak et al., "Low-Termperature (10K-300K) Characterization of MOVPE-Grown Cavity Surface-Emitting Lasers", Photon. Tech. Lett., Vol. 7, No. 10, pp. 1110-1112 1995.		n Vertical- 12, October					
	ΑI	Huffaker et al., "Lasin Spacer Layers and Lat April 3, 1995.	g Characteristic eral Index Con	es of Low Threshold M finement", <u>Appl. Phys.</u>	icrocavity l Lett., Vol.	Layers Usi 66, No. 14	ng Half-Wave , pp.1723-1725,	
U	AJ	K.L. Lear et al., "Selectively Oxidized Vertical Cavity Surface-Emitting Lasers with 50% Power Conversion Efficiency", Elec. Lett., Vol. 31, No. 3 pp. 208-209, February 2, 1995.						
	AK	Lehman et al., "High I Singlemode VCSELs"	Frequency Mod , Electronic Let	ulation Characteristics tters, vol. 31, No. 15, Ju	of Hybrid I uly 20, 199	Dielectric/ 5, pp. 1251	AlGaAs Mirror -1252.	
	AL	Magnusson, "Integrati Research Center, Depa 1997.	on of Guided-Nartment of Elect	Mode Resonance Filters trical Engineering, Uni	and VCSE versity of T	Ls", Electo exas at Arl	o-Optics lington, May 6,	
	AM			GaAs Mirror Spatially-I b. 8, pp. 921-923, Febru			Surface Emitting	
	AN	Morgan et al., "One W pp. 206-207, January 2		vity Surface Emitting I	Las <b>e</b> r", <u>Elec</u>	tron. Lett.,	Vol. 29, No. 2,	

FORM	1 PTC	D-1449	Atty. Docket No.: 1100.1114101 (H16-26549)	Serial No.: 09/751,423	
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	-W	DISCLOSURE STATEMENT	Filing Date	Group Art:	
NU6 1 97			December 29, 2000	2872	
TRADE	<b>100</b>				
CALL	ÃO	Morgan et al., "Producible GaAs-based MOVP Lasers with Record Performance", Elec. Lett.,	E-Grown Vertical-Cavity Top Vol. 31, No. 6, pp. 462-464, N	-Surface Emitting farch 16, 1995.	
	ΑP	Morgan et al., "Spatial-Filtered Vertical-Cavity 138-139.	Top Surface-Emitting Lasers	", CLEO, 1993, pp.	
)	AQ	Morgan et al., "Vertical Cavity Surface Emittin paper, SPIE, Vol. 2683-04, OE LASE 96; Phot Semiconductor Lasers, (SPIE< Bellingham, W.	onics West: Frabrication, Tes	e,", Invited ting and Reliablity of	
	AR	S.S. Wang and R. Magnusson, "Multilayer Wa- 14, pp. 2414-20, 1995.	veguide-Grating Filters", App	<u>l. Opt.,</u> Vol. 34, No.	
	AS	S.S. Wang and R. Magnusson, "Theory and Ap Appl. Opt., Vol. 32, No. 14, pp. 2606-13, 1993.		esonance Filters",	
	TA	Schubert, "Resonant Cavity Light-Emitting Dic February 24, 1992.	ode", Appl. Phys. Lett., Vol. 6	0, No. 8, pp. 921-923,	
	AU	Y. M. Yang et al., "Ultralow Threshold Current with Selective Oxidation", Elect. Lett., Vol. 31	Vertical Cavity Surface Emit , No. 11, pp. 886-888, May 25	ting Lasers Obtained 5, 1995.	
	ΑV	Yablonovitch et al., "Photonic Bandgap Structu 295, February 1993.	res", J. Opt. Soc. Am. B., Vol	. 10, No. 2, pp. 283-	
	AW	Young et al., "Enhanced Performance of Offset Emitting Lasers", IEEE J. Quantum Electron.,	-Gain High Barrier Vertical-C Vol. 29, No. 6, pp. 2013-2022,	avity Surface- June 1993.	
	AX	Smith, R.E. et al., "Polarization-Sensitive Subw Semiconductor for 975 NM, Optics Letters, Vo	vavelength Antireflection Surfall. 21, No. 15, August 1, 1996,	aces on a pp. 1201-1203.	
	AY	Suning Tang et al., "Design Limitations of High on Arrays of Vertical Cavity Surface-Emitting I Journal of Lightwave Technology, Vol. 12, No.	Laser Diodes, Microlenses, an	d Photodetectors",	
	AZ	Cox, J. A., et al., "Guided Mode Grating Reson of the SPIE, The International Society for Optic Technologies and Applications V, San Jose, Ca 71.	cal Engineering, Diffractive an	d Holographic Device	
1	ВА	Martinsson et al., "Transverse Mode Selection i Surface-Emitting Lasers Using a Shallow Surfa 1536-1538 (1999).	n Large-Area Oxide-Confined ce Relief', <u>IEEE Photon. Tecl</u>	l Vertical-Cavity nnol. Lett., 11(12),	

EXAMINER: Description with the Date Considered: Date Cons

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TRAC	EMARIA				
Ofic	СМ	Jewell et al., "Surface-Emitting Microlasers for Optical Engineering, Vol. 29, No. 3, March 19	r Photonic Switching and Inter 90, pp. 210-214.	chip Connections",	
2.)	CN	Kishino et al., "Resonant Cavity-Enhanced (RC Electronics, Vol. 27, No. 8, pp. 2025-2034.	CE) Photodetectors", IEEE Jou	mal of Quantum	
, ·	со	Kuchibhotla et al., "Low-Voltage High Gain R Phototonics Technology Letters, Vol. 3, No. 4,	esonant_Cavity Avalanche Phopp. 354-356.	otodiode", <u>IEEE</u>	
, [	CP	Lai et al., "Design of a Tunable GaAs/AlGaAs Photodetector", IEEE Journal of Quantum Elec	Multiple-Quantum-Well Reso stronics, Vol. 30, No. 1, pp. 10	nant Cavity 8-114.	
> \	cq	Lee et al., "Top-Surface Emitting GaAs Four-C Electronics Letters, Vol. 24, No. 11, May 24, 1		at 0-85 um",	
, \.	CR	Lehman et al., "High Frequency Modulation C Singlemode VCSELs", Electronic Letters, vol.	haracteristics of Hybrid Dielec 31, No. 15, July 20, 1995, pp.	tric/AlGaAs Mirror 1251-1252.	
	cs	Miller et al., "Optical Bistability Due to Increase 1984, pp. 162-164.	sing Absorption", Optics Lette	<u>rs,</u> Vol. 9, No. 5, May	
·	СТ	Morgan et al., "200 C, 96-nm Wavelength Ran MOVPE-Grown Vertical Cavity Surface-Emitt Vol. 7, No. 5, May 1995, pp. 441-443.	ge, Continuous-Wave Lasing ting Lasers", <u>IEEE Photonics T</u>	rom Unbonded GaAs echnology Letters,	
	CU	Jiang et al., "High-Frequency Polarization Self- Lasers", Appl. Phys. Letters, Vol. 63, No. 26, I	-Modulation in Vertical-Cavity December 27, 1993, pp. 2545-2	Surface-Emitting	
	cv	Morgan et al., "High-Power Coherently Couple Array", Appl. Phys Letters, Vol 61, No. 10, Sep	ed 8x8 Vertical Cavity Surface otember 7, 1992, pp. 1160-116	Emitting Laser 2.	
-	cw	Morgan et al., "Hybrid Dielectric/AlGaAs Mirr Emitting Laser", Appl. Phys. Letters, Vol. 66, 1			
	cx	Morgan et al., "Novel Hibrid-DBR Single-Mod Record Low Voltage", 2 pages, dated prior to D		ing VCSEL with	
	ÇY	Morgan et al., "Progress and Properties of High Laser Arrays", SPIE, Vo. 1850, January 1993, p	n-Power Coherent Vertical Cavop, 100-108.	vity Surface Emitting	
	CZ	Morgan et al., "Progress in Planarized Vertical SPIE, Vol. 1562, July 1991, pp. 149-159.	Cavity Surface Emitting Laser	Devices and Arrays",	
	DA	Morgan et al., "Submilliamp, Low-Resistance, Vertical-Cavity Surface Emitting Lasers", Hone	Continuous-Wave, Single-Mo	de GaAs Planar ne 6, 1995.	

FORM PT	O-1449	Atty. Doc!	Atty. Docket No.: Serial No.: 1100.1114101 (H16-26549) 09/751,423				
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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION AUG 1 9 2003 POISCLOSURE STATEMENT Filing Date  Group Art:						Group Art:	
	§			December	29, 2000	]	2872
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The BY	5,778,018	07/07/1998	Yoshikawa	et al.	372	45	
BZ	5,818,066	10/06/1998	Duboz		257	21	
CA	5,903,590	05/11/1999	Hadley et al		372	96	j
СВ	5,940,422	08/17/1999	Johnson		372	45	
cc	5,978,401	11/02/1999	Morgan		372	50	
CD	6,055,262	04/25/2000	Cox et al.		372	96	<u> </u>
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	OTHER	R ART (Includi	ng Author, Tit	ile, Date, Pert	inent Pages	, Etc.)	
CF	CF Banwell et al., "VCSE Laser Transmitters for Parallel Data Links", IEEE Journal of Quantum Electronics, Vol. 29, No. 2, February 1993, pp. 635-644.						
cG	Catchmark et al., Lasers", CLEO 19	"High Temper 993, p. 138.	ature CW Ope	ration of Ver	tical Cavity	Top S	urface-Emitting
СН	Chemla et al., "No Nonlinearities and 120.	onlinear Optica 1 Instabilities in	al Properties of n Semiconduct	f Semiconduc tors, Academ	tor Quantu	m Well	ls", <u>Optical</u> yright 1988, pp. 83-
CI	Choa et al., "High Technology Lette	ı-Speed Modul r, Vol. 3, No. 8	ation of Vertices, August 1991	al-Cavity Su , pp. 697-699	rface-Emitt ).	ing Las	sers", <u>IEEE Photonics</u>
G. G. Ortiz, et al., "Monolithic Integration of In0.2 GA0.8As Vertical Cavity Surface-Emitting Lasers with Resonance-Enhanced Quantum Well Photodetectors", Electronics Letters, Vol. 32, No. 13, June 20, 1996, pp. 1205-1207.							
l cr	CK Graf, Rudolph, Modern Dictionary of Electronics, 6th ed., Indiana: Howard W. Sams & Company, 1984, p. 694.						
	1984, p. 694.						

FORM PTO-1449	Atty. Docket No.: 1100.1114101 (H16-26549)	Serial No.: 09/751,423
.  18 FROF PATENTS AND DURI ICATIONS FOR	Applicant: Robert A. Morg	gan et al.
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	December 29, 2000	2872
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q	Me		DB	Morgan et al., "Transverse Mode Control of Vertical-Cavity Top-Surface Emitting Lasers", <u>IEEE Photonics Technology Letters</u> , Vol. 4, No. 4, April 1993, pp. 374-377.
C.			рc	Morgan et al., "Vertical Cavity Surface Emitting Laser Arrays: Come of Age,", Invited paper, <u>SPIE</u> , Vol. 2683-04, OE LASE 96; Photonics West: Frabrication, Testing and Reliablity of Semiconductor Lasers, (SPIE< Bellingham, WA, 1996).
<i>O</i> ''			DD ·	Morgan et al., "Vertical-Cavity Surface-Emitting Laser Arrays" SPIE, Vol. 2398, February 1995, pp. 65-93.
´∂ .			DE	Morgan, "High-Performance, Producible Vertical Cavity Lasers for Optical Interconnects", <u>High Speed Electronics and Systems</u> , Vol. 5, No. 4, December 1994, pp. 65-95.
C'			DF	Morgan, "Transverse Mode Control of Vertical-Cavity Top-Surface Emitting Lasers", <u>IEEE Phot.</u> Tech. Lett., Vol. 4, No. 4., p. 374, April 1993.
8			DG	Nugent et al., "Self-Pulsations in Vertical-Cavity Surface-Emitting Lasers", <u>Electronic Letters</u> , Vol. 31, No. 1, January 5, 1995, pp. 43-44.
Ø			DH	U.S. Patent Application Serial No. 09/751,422, filed December 29, 2000, entitled "Resonant Reflector for Use with Optoelectronic Devices".

EXAMINER: Vougla Will DATE CONSIDERED: 1 Lec 03